

Silicon NPN Power Transistor

2SC2665

DESCRIPTION

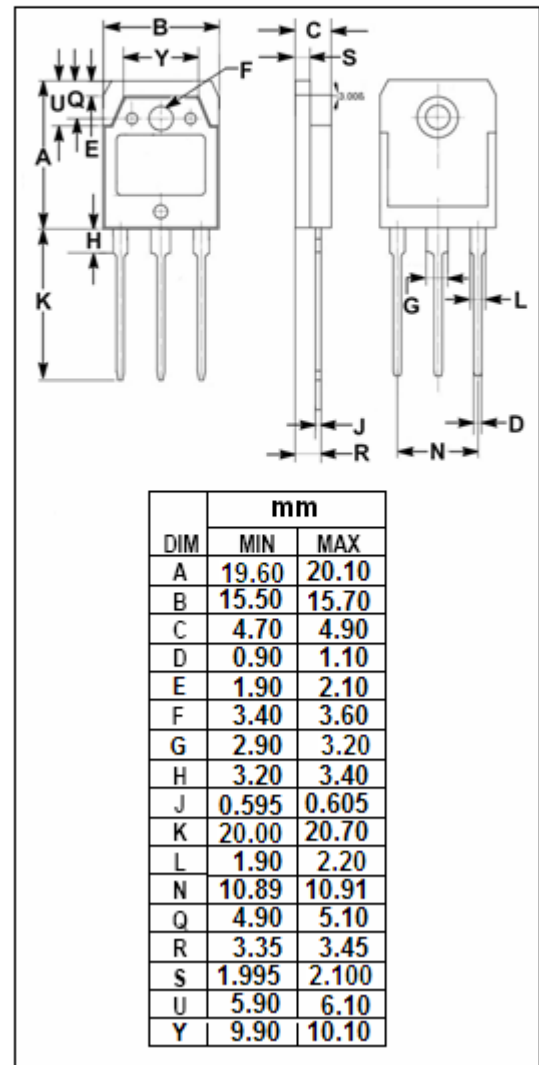
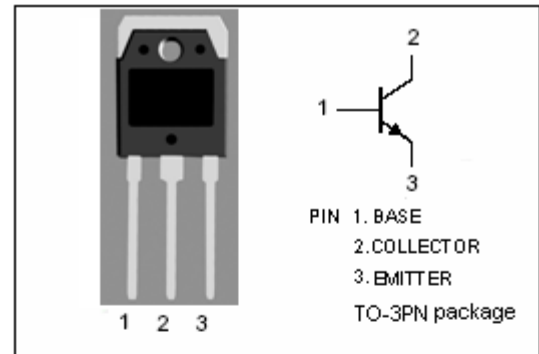
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80V(\text{Min})$
- Wide Area of Safe Operation

APPLICATIONS

- Designed for audio frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	4	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	55	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-40~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}$; $R_{BE}=\infty$	80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}$; $I_E=0$	100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}$; $I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}$; $I_B=0.3\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=100\text{V}$; $I_E=0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=4\text{V}$; $I_C=0$			100	μA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}$; $V_{CE}=4\text{V}$	40			
h_{FE-2}	DC Current Gain	$I_C=4\text{A}$; $V_{CE}=4\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}$; $V_{CE}=5\text{V}$		10		MHz